1. General description

Dual Standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- · Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Limiting values	s FET1 and FET2					
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	21	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	64	W
Static characte	eristics FET1 and FET2					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 11	-	12.5	16.7	mΩ
Dynamic chara	acteristics FET1 and FE	T2				
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 64 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	10.4	-	nC
Source-drain d	liode FET1 and FET2					
Q _r	recovered charge	I_S = 10 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C	-	37.1	-	nC



Dual N-channel 80 V, 17 $m\Omega$ standard level MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4	
8	D1	drain1	LFPAK56D (SOT1205)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK7K17-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K17-80E	71780E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Limiting valu	ues FET1 and FET2				'	
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	64	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	21	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	15	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	84	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode FET1 and FET2			1	<u> </u>	
Is	source current	T _{mb} = 25 °C		-	21	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	84	Α
Avalanche r	uggedness FET1 and FET2		'	1	1	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 21 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1] [2]	-	116	mJ

- Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$ Refer to application note AN10273 for further information.

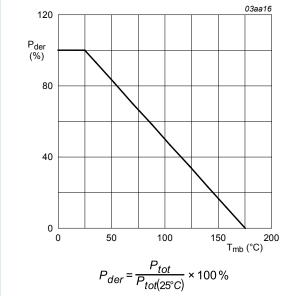


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

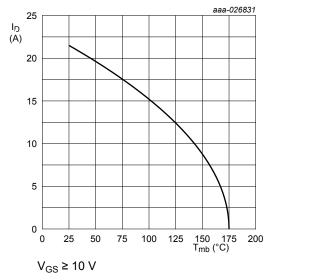
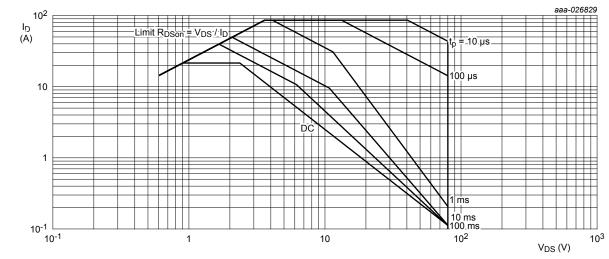


Fig. 2. Continuous drain current as a function of mounting base temperature, FET1 and FET2

BUK7K17-80E

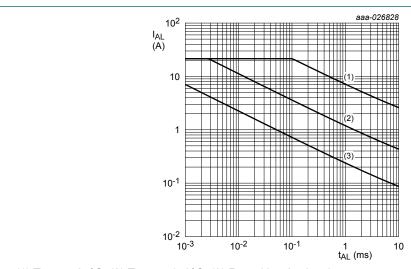
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Dual N-channel 80 V, 17 mΩ standard level MOSFET



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1 and FET2



(1) $T_{i \text{ (init)}} = 25^{\circ}\text{C}$; (2) $T_{i \text{ (init)}} = 150^{\circ}\text{C}$; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

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Dual N-channel 80 V, 17 $m\Omega$ standard level MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.36	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

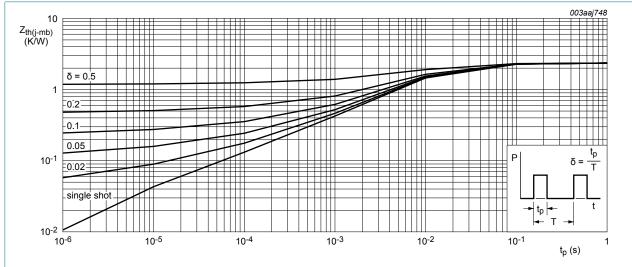


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration, FET1 and FET2

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10. Characteristics

Table 7. Characteristics

drai brea	0 μA; $V_{GS} = 0$ V; $T_{j} = 25$ °C 0 μA; $V_{GS} = 0$ V; $T_{j} = -55$ °C 0 μA; $V_{DS} = V_{GS}$; $T_{j} = 25$ °C; Fig. 9; 0 μA; $V_{DS} = V_{GS}$; $T_{j} = -55$ °C;	drain-source breakdown voltage gate-source threshold voltage	80 72	-	-	1
brea gate	$^{\circ}$ µA; $^{\circ}$ V _{GS} = 0 V; $^{\circ}$ T _j = -55 °C NA; $^{\circ}$ V _{DS} =V _{GS} ; $^{\circ}$ T _j = 25 °C; Fig. 9;	breakdown voltage gate-source threshold			_	T.,
gate	A; $V_{DS} = V_{GS}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 9;	gate-source threshold	72			V
_	,	1 ~		-	-	V
	$^{1}A; V_{DS} = V_{GS}; T_{j} = -55 ^{\circ}C;$		2.4	3	4	V
			-	-	4.5	V
	$^{1}A; V_{DS} = V_{GS}; T_{j} = 175 ^{\circ}C;$		1	-	-	V
drai	0 V; V _{GS} = 0 V; T _j = 25 °C	drain leakage current	-	0.02	1	μA
	0 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
gate	0 V; V _{DS} = 0 V; T _j = 25 °C	gate leakage current	-	2	100	nA
	20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
	0 V; I _D = 10 A; T _j = 25 °C;	drain-source on-state resistance	-	12.5	16.7	mΩ
	0 V; I _D = 10 A; T _j = 175 °C;		-	-	42	mΩ
acter		naracteristics FET1 and FE	•	'	_	
tota	A; V _{DS} = 64 V; V _{GS} = 10 V;	total gate charge	-	32.4	-	nC
gate	°C; <u>Fig. 13</u> ; <u>Fig. 14</u>	gate-source charge	-	7.1	-	nC
gate		gate-drain charge	-	10.4	-	nC
inpu	5 V; V _{GS} = 0 V; f = 1 MHz;	input capacitance	-	1701	2262	pF
out	°C; <u>Fig. 15</u>	output capacitance	-	174	208	pF
		reverse transfer capacitance	-	104	142	pF
turn	0 V; R _L = 5 Ω; V _{GS} = 10 V;	turn-on delay time	-	8.1	-	ns
rise	: 5 Ω; T _j = 25 °C	rise time	-	11.1	-	ns
turn		turn-off delay time	-	22.5	-	ns
fall		fall time	-	13.4	-	ns
diode		in diode FET1 and FET2	'			
sou	A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	source-drain voltage	-	0.8	1.2	V
reve	A; dl _S /dt = -100 A/μs; V _{GS} = 0 V;	reverse recovery time	-	30.1	-	ns
	5 V; T _i = 25 °C	recovered charge	-	37.1	-	nC
turn rise turn fall diode	$= 5 Ω; T_j = 25 °C$ A; $V_{GS} = 0 V; T_j = 25 °C; Fig. 16$	capacitance turn-on delay time rise time turn-off delay time fall time in diode FET1 and FET2 source-drain voltage reverse recovery time	- - -	8.1 11.1 22.5 13.4 0.8 30.1	- - -	

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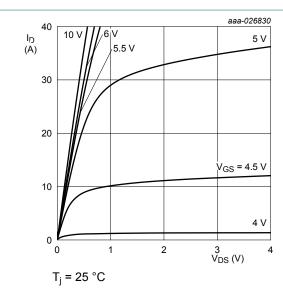


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

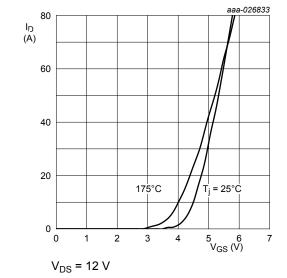


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values, FET1 and FET2

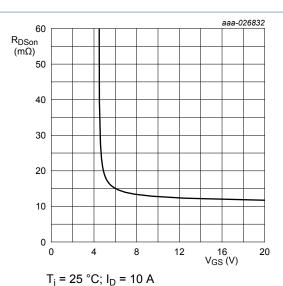
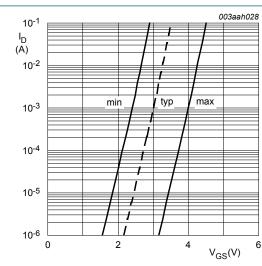


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

Fig. 9. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2

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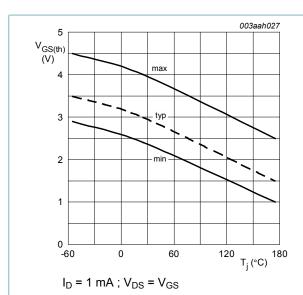


Fig. 10. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2

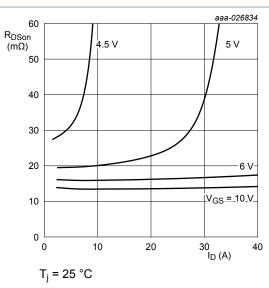


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values, FET1 and FET2

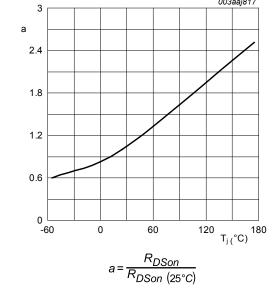


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1 and FET2

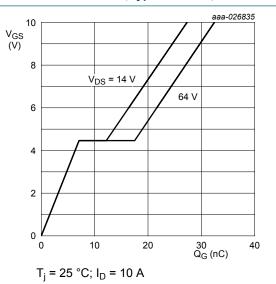


Fig. 13. Gate-source voltage as a function of gate charge; typical values, FET1 and FET2

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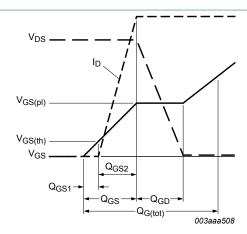
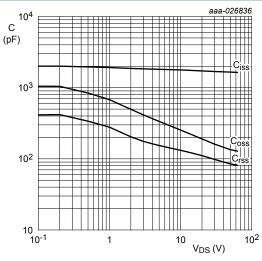
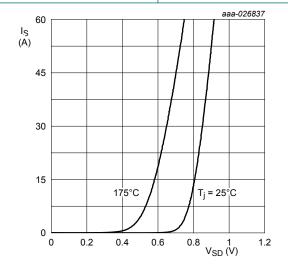


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1 and FET2



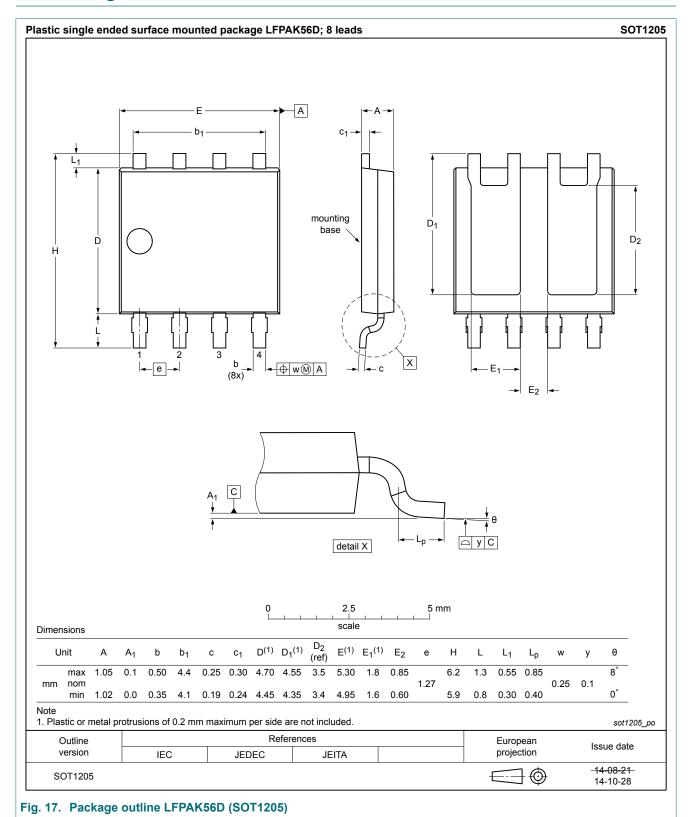
 $V_{GS} = 0 V$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1 and FET2

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11. Package outline



Product data sheet

Dual N-channel 80 V, 17 mΩ standard level MOSFET

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BUK7K17-80E

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